

CLAIM AMENDMENTS:

1. (Currently Amended) An electronic device comprising:

a substrate;

a bump of a first metal material provided on a surface of the substrate;

a bonding film of a second metal material provided on a top surface of the bump for bonding the electronic device to an electrical connection portion of a second device, ~~the second metal material having a lower melting point in an elemental state than an alloy of the first metal material and the second metal material;~~ device; and

a diffusion prevention film of a third metal material provided between the top surface of the bump and the bonding ~~film as film,~~ the diffusion prevention film partially covering at least part of the top surface of the bump, ~~the third metal material having a lower diffusion coefficient than the second metal material with respect to the first metal material.~~ and the bonding film having a first portion in direct contact with the diffusion prevention film and a second portion in direct contact with the top surface of the bump.

2-3. (Canceled)

4. (Currently Amended) ~~An~~ The electronic device as set forth in claim 1, wherein the substrate is a semiconductor substrate, and the electronic device is a semiconductor chip.

5. (Currently Amended) ~~A~~ The electronic device as set forth in claim 1, wherein the substrate is a wiring board having a wiring conductor provided on an insulating substrate, and

the bump is provided on the wiring board and connected to the wiring conductor.

6. (Currently Amended) A semiconductor device of a chip-on-chip structure comprising a first semiconductor chip and a second semiconductor chip respectively having bumps and connected to each other with the bumps thereof bonded to each other, wherein at least one of the first semiconductor chip and the second semiconductor chip is ~~an~~ the electronic device as recited in claim 4.

7. (Currently Amended) A semiconductor device comprising:
a wiring board having a wiring conductor provided on an insulating substrate; and
~~an~~ the electronic device as recited in claim 4, the electronic device being connected to the wiring conductor with ~~a~~ the bump thereof opposed to the wiring board.

8. (Withdrawn) A semiconductor device production method for producing a semiconductor device by bonding a semiconductor chip onto a semiconductor substrate via a bump,

the bump being provided on a surface of at least one of the semiconductor substrate and the semiconductor chip, and composed of a first metal material,

the bump having a bonding film of a second metal material provided on a top surface thereof, the second metal material having a lower melting point in an elemental state than an alloy of the first metal material and the second metal material,

the bump further having a diffusion prevention film of a third metal material provided between the top surface of the bump and the bonding film as covering a part of the top surface of the bump and uncovering the rest of the top surface, the third metal material having a lower diffusion coefficient than the second metal material with respect to the first metal material,

the bonding film having a portion present on the diffusion prevention film and a portion contacting the top surface of the bump,

the method comprising the steps of:

temporarily bonding the semiconductor chip onto the semiconductor substrate with the semiconductor chip being placed on the semiconductor substrate with the intervention of the bump by heating the bonding film at a first temperature which is not lower than the melting point of the second metal material in the elemental state and lower than the melting point of the alloy of the first metal material and the second metal material; and

firmly bonding the semiconductor chip onto the semiconductor substrate after the temporary bonding step by heating the bonding film at a second temperature which is not lower than the melting point of the alloy of the first metal material and the second metal material.

9. (Withdrawn) A semiconductor device production method as set forth in claim 8, wherein

the firm bonding step is performed after a plurality of semiconductor chips are temporarily bonded onto the semiconductor substrate.

10. (New) The electronic device as set forth in claim 1, wherein the second metal material has a lower melting point in an elemental state than an alloy of the first metal material and the second metal material.

11. (New) The electronic device as set forth in claim 1, wherein the third metal material has a lower diffusion coefficient than the second metal material with respect to the first metal material.

12. (New) The electronic device as set forth in claim 1, wherein the first metal material is Au or Cu.

13. (New) The electronic device as set forth in claim 1, wherein the second metal material is Sn, In, or an Sn-In alloy.

14. (New) The electronic device as set forth in claim 1, wherein the third material is TiW.

15. (New) An electronic device comprising:
a substrate;

a bump of a first metal material provided on a surface of the substrate;

a bonding film of a second metal material provided on a top surface of the bump to bond the electronic device to an electrical connection portion of a second device; and

a diffusion prevention film of a third metal material provided between the top surface of the bump and the bonding film, the diffusion prevention film partially covering the top surface of the bump, and the bonding film having a first portion in direct contact with the diffusion prevention film and a second portion in direct contact with the top surface of the bump.